

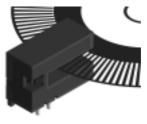
Transmissive Optical Sensor with Phototransistor Output

Description

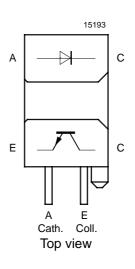
This device has a compact construction where the emittig-light sources and the detectors are located face-to-face on the same optical axis. The operating wavelength is 950 nm. The detector consists of a phototransistor.

Applications

- Position sensor for shaft encoder
- Detection of opaque material such as paper, cards, magnetic tapes etc.
- Limit switch for mechanical motions in VCR
- Read/ write head position in data storage equipment
- General purpose wherever the space is limited







Features

- Gap 2.7 mm
- Package height: 9 mm
- Aperture 0.5 mm
- Plastic polycarbonate housing
- Current Transfer Ratio (CTR) of typical 7.5%
- Designed for horizontal moving objects

Order Instruction

Ordering Code	Resolution (mm) / Aperture (mm)	Remarks
TCST5250	0.4 / 0.5	



Absolute Maximum Ratings

Input (Emitter)

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V _R	6	V
Forward current		١ _F	60	mA
Forward surge current	t _p ≤ 10 μA	I _{FSM}	3	А
Power dissipation	$T_{amb} \le 25^{\circ}C$	PV	100	mW
Junction temperature		T _j	100	°C

Output (Detector)

Parameter	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V _{CEO}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		Ι _C	100	mA
Power dissipation	T _{amb} ≤ 25 °C	Pv	150	mW
Junction temperature		Τ _i	100	°C

Coupler

Parameter	Test Conditions	Symbol	Value	Unit
Total power dissipation	T _{amb} ≤ 25 °C	P _{tot}	250	mW
Operation temperature range		T _{amb}	-25 to +85	°C
Storage temperature range		T _{stq}	-40 to +100	°C
Soldering temperature	1.6 mm from case, $t \le 5 s$	T _{sd}	260	°C

Electrical Characteristics (T_{amb} = 25°C)

Input (Emitter)

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	I _F = 60 mA	VF		1.25	1.5	V
Junction capacitance	V _R = 0, f = 1 MHz	Ci		50		рF

Output (Detector)

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector emitter voltage	$I_{\rm C} = 1 \rm{mA}$	V _{CEO}	70			V
Emitter collector voltage	I _E = 10 μA	V _{ECO}	7			V
Collector dark current	$V_{CE} = 25 \text{ V}, \text{ I}_{F} = 0, \text{ E} = 0$	I _{CEO}		10	100	nA

Coupler

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector current	V _{CE} = 10 V, I _F = 20 mA	I _C	0.5	1.5	15	mA
Collector emitter saturation voltage	$I_{\rm F}$ = 20 mA, $I_{\rm C}$ = 0.2 mA	V _{CEsat}			0.4	V



Switching Characteristics

Parameter	Test Conditions	Symbol	Тур.	Unit
Turn-on time	I_C = 1 mA, V_{CE} = 5 V, R_L = 100 Ω (see figure 1)	t _{on}	15.0	μs
Turn-off time		t _{off}	10.0	μs

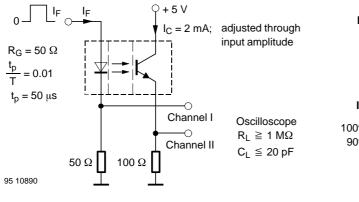


Figure 1. Test circuit

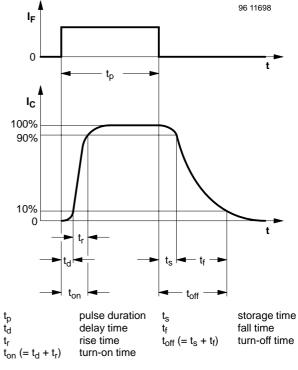


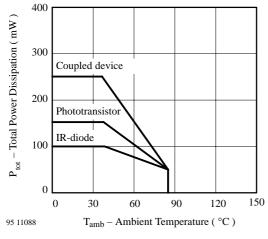
Figure 2. Switching times

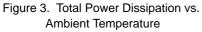
TCST5250



Vishay Telefunken

Typical Characteristics (T_{amb} = 25°C, unless otherwise specified)





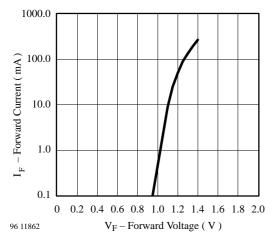


Figure 4. Forward Current vs. Forward Voltage

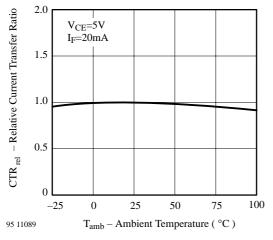


Figure 5. Relative Current Transfer Ratio vs. Ambient Temperature

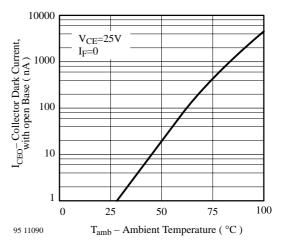


Figure 6. Collector Dark Current vs. Ambient Temperature

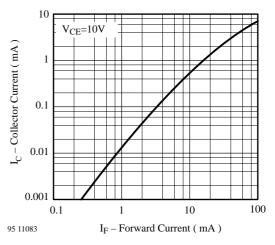


Figure 7. Collector Current vs. Forward Current

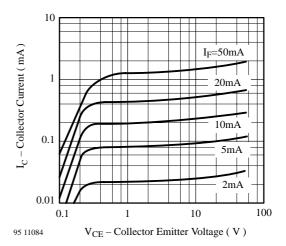


Figure 8. Collector Current vs. Collector Emitter Voltage



TCST5250 Vishay Telefunken

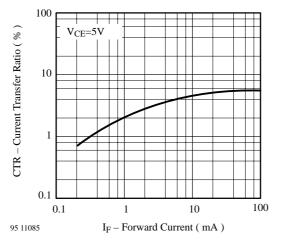


Figure 9. Current Transfer Ratio vs. Forward Current

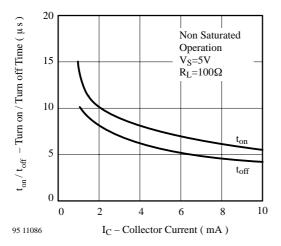


Figure 10. Turn on / off Time vs. Collector Current

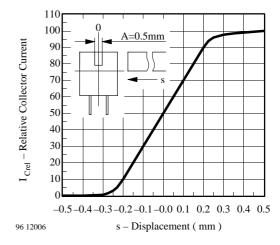
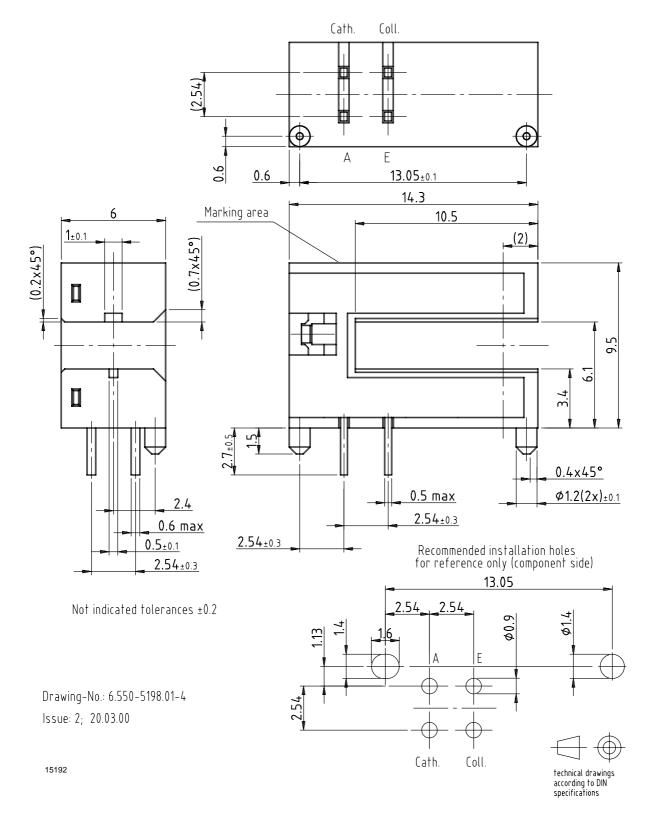


Figure 11. Relative Collector Current vs. Displacement



Dimensions of TCST5250 in mm





Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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